

20-25GHz Low Noise Amplifier

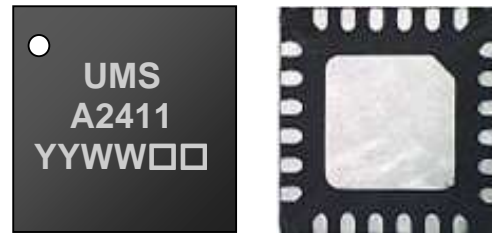
GaAs Monolithic Microwave IC in SMD package

Description

The CHA2411-QDG is a K band low noise amplifier providing 26 dB gain from a single bias supply +5V with a noise figure of 2.5 dB. All the active devices are self biased on chip.

The circuit is manufactured with a pHEMT process 0.25µm.

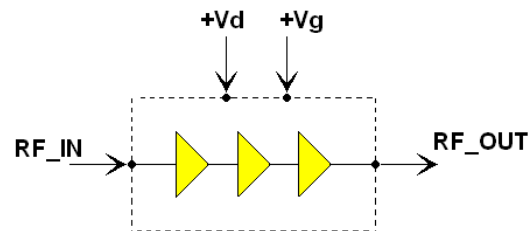
It is available in lead-free SMD package.



Functional diagram

Main Features

- 20-25GHz Bandwidth
- Excellent 2.5dB Noise Figure
- 26 dB ± 2dB stable Gain vs Ttemperature
- +5V single Supply
- 24L-QFN 4x4 SMD leadless package



Main Characteristics

Tamb = +25°C

| Parameters | Min | Typ | Max | Unit |
|----------------------------|-----|-----|-----|------|
| Frequency range | 20 | | 25 | GHz |
| Small signal Gain | 22 | 26 | 30 | dB |
| SSB Noise figure | | 2.5 | | dB |
| Input / Output Return Loss | | 15 | | dB |

ESD Protection : Electrostatic discharge sensitive device. Observe handling precautions !

Electrical Characteristics

Full temperature range

| Symbol Pins | Parameters | Min | Typ | Max | Unit |
|-----------------|--|-----|-----------|-----|------|
| Fop | Operating frequency range | 20 | | 25 | GHz |
| G | Small signal Gain | 22 | 26 | 30 | dB |
| $\Delta G(Fop)$ | Gain variation @ frequency range | | ± 0.5 | | dB |
| $\Delta G(T)$ | Gain variation @ temperature range | | ± 2 | | dB |
| NF | SSB Noise figure | | 2.5 | | dB |
| S11 S22 | Input / Output Return | | -10 | | dB |
| P.1dB In | Input Power at 1 dB Gain Compression @24GHz | | -14 | | dBm |
| IP3 In | Input IP3 @24GHz | | -7.5 | | dBm |
| Pout_sat | Saturated Output Power @24GHz | | 13.5 | 15 | dBm |
| +Vd, +Vg | Supply Voltage | | 5 | | V |
| +I | Supply Current | | 43 | 55 | mA |
| Top | Operating temperature range | -40 | 25 | 100 | °C |

Remark

These performance has been obtained with the chip in QFN package mounted on the recommended boards (ref. 95541 & 95581) described in the document. These performances are highly dependent on this environment.

Absolute Maximum Ratings (1)

| Symbol | Parameters | Values | Unit |
|----------|------------------------------------|-------------|------|
| +Vg, +Vd | Maximum positive supply voltage | 6 | V |
| +I | Maximum positive supply current | 65 | mA |
| Pin | Maximum peak input power overdrive | -5 | dBm |
| Top | Operating temperature range | -40 to +100 | °C |
| Tstg | Storage temperature range | -55 to +125 | °C |

(1) Operation of this device above any one of these parameters may cause permanent damage.
Duration < 1s

Device thermal performances

All the figures given in this section are obtained assuming that the QFN device is cooled down only by conduction through the package thermal pad (no convection mode considered). The temperature is monitored at the package back-side interface (Tcase) as shown below. The system maximum temperature must be adjusted in order to guarantee that Tcase remains below than the maximum value specified in the next table. So, the system PCB must be designed to comply with this requirement.

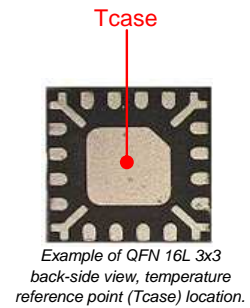
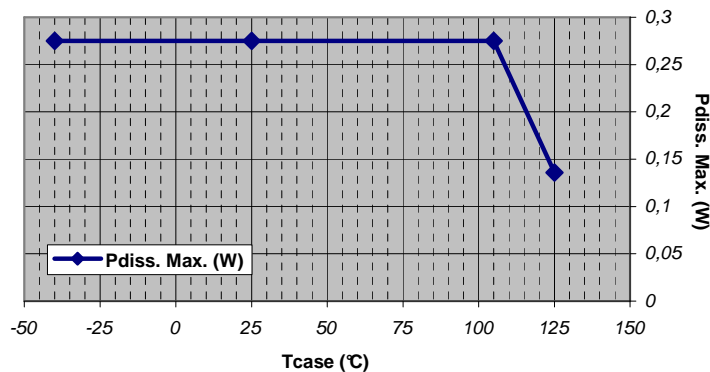
A derating must be applied on the dissipated power if the Tcase temperature can not be maintained below than the maximum temperature specified (see the curve Pdiss. Max) in order to guarantee the nominal device life time (MTTF).

| DEVICE THERMAL SPECIFICATION : CHA2411-QDG | | |
|---|---|-----------|
| Recommended max. junction temperature (Tj max) | : | 145 °C |
| Junction temperature absolute maximum rating | : | 175 °C |
| Max. continuous dissipated power @ Tcase= 105 °C | : | 0,275 W |
| => Pdiss derating above Tcase ⁽¹⁾ = 105 °C | : | 7 mW/°C |
| Junction-Case thermal resistance (Rth J-C) ⁽²⁾ | : | <143 °C/W |
| Min. package back side operating temperature ⁽³⁾ | : | -40 °C |
| Max. package back side operating temperature ⁽³⁾ | : | 105 °C |
| Min. storage temperature | : | -55 °C |
| Max. storage temperature | : | 125 °C |

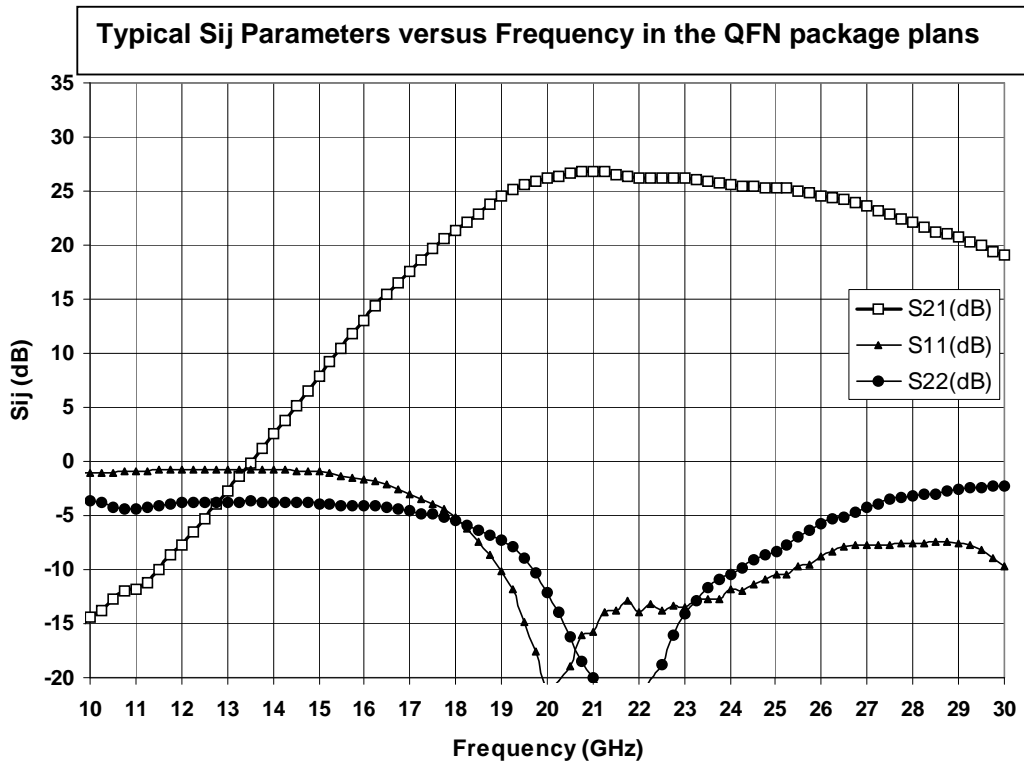
(1) Derating at junction temperature constant = Tj max

(2) Rth J-C is calculated for a worst case where the **hotter junction** of the MMIC is considered.

(3) Tcase=Package back side temperature measured under the die-attach-pad (see the drawing below).



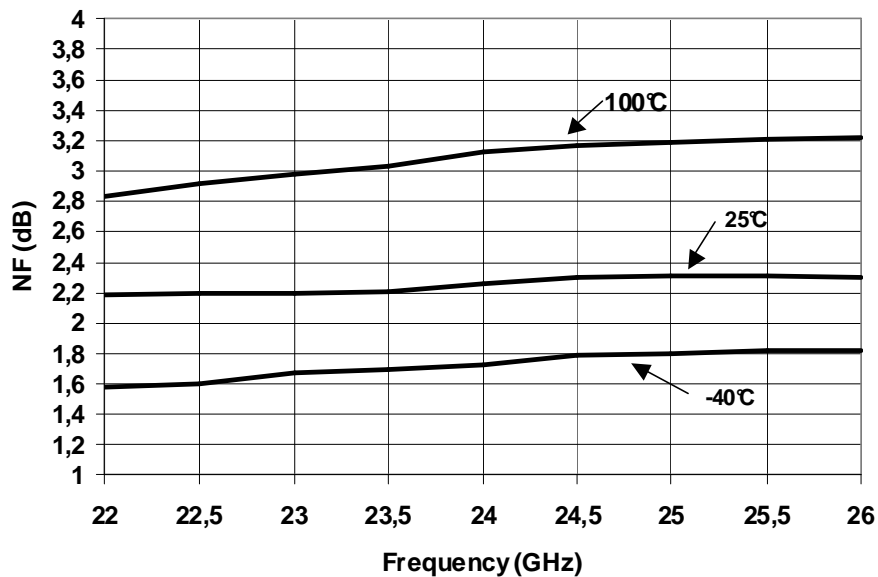
Typical QFN measurements on board 95581 (QFN plan)



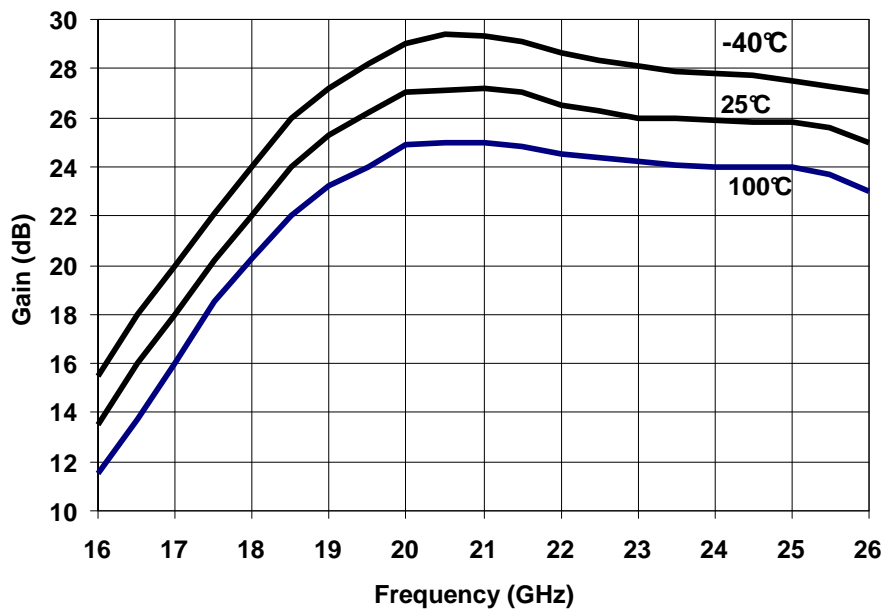
Typical QFN measurements on board 95541 (QFN plan)

Vs = versus

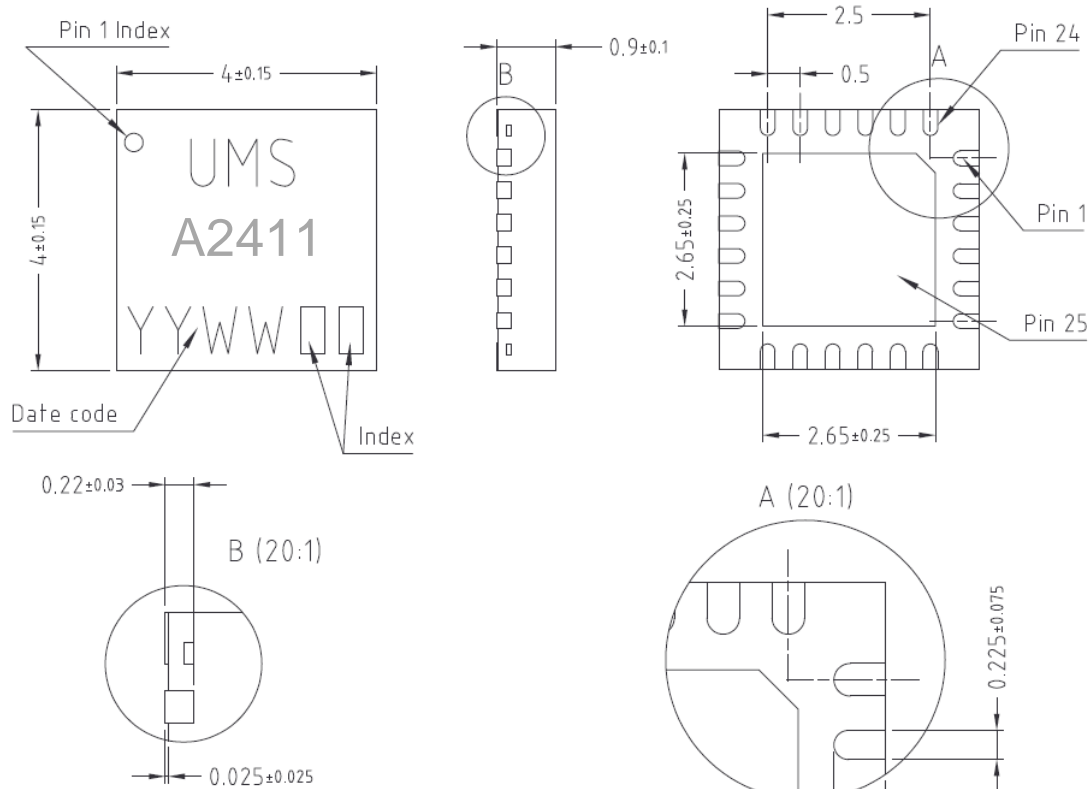
Noise Figure versus Frequency



Gain versus Frequency



QFN Outline (1)



Units : mm

From the standard : JEDEC MO-220 [VGGD]

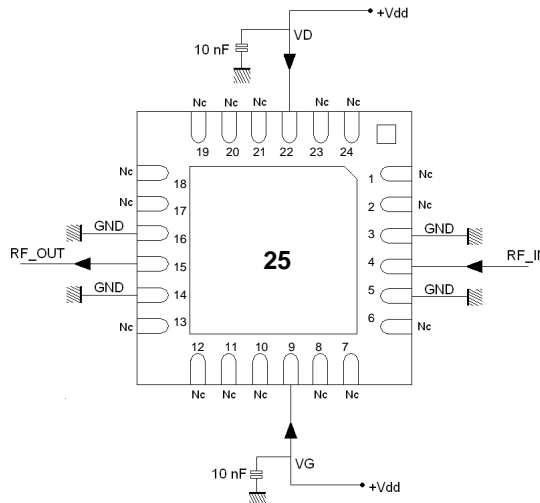
Matt tin, Lead free (Green)

⁽¹⁾The package outline drawing included to this data-sheet is given for indication. Refer to the application note AN0017 available at <http://www.ums-gaas.com> for exact package dimensions.

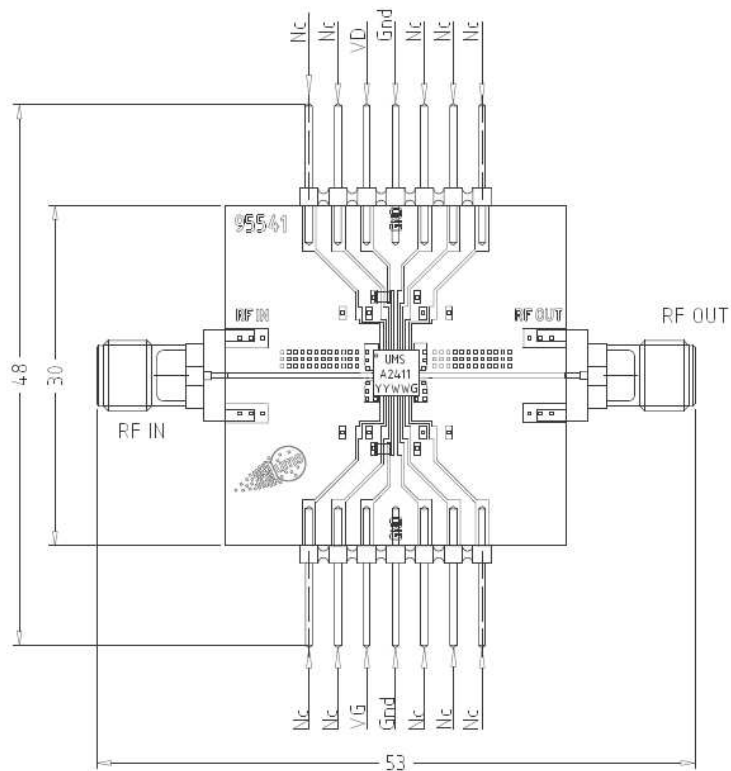
Pin-out description

| Pin number | Pin name | Symbol Name | Description |
|---|----------|-------------|-------------------------------|
| 4 | RFin | RF_IN | Control Voltage port |
| 15 | RFOut | RF_OUT | RF1 Input/Output ports |
| 22 | VD | +Vd | Positive Drain supply voltage |
| 9 | VG | +Vg | Positive Gate supply voltage |
| 3, 5, 14, 16, 25 | GND | GND | Ground |
| 1, 2, 6, 7, 8, 10, 11, 12, 13, 17, 18, 19, 20, 21, 23, 24 | Nc | Nc | Not connected |

External Components and bias configuration (recommended)



Recommended Test Fixture (Ref. 95541) for measurements over Temperature Range (Unit=mm)



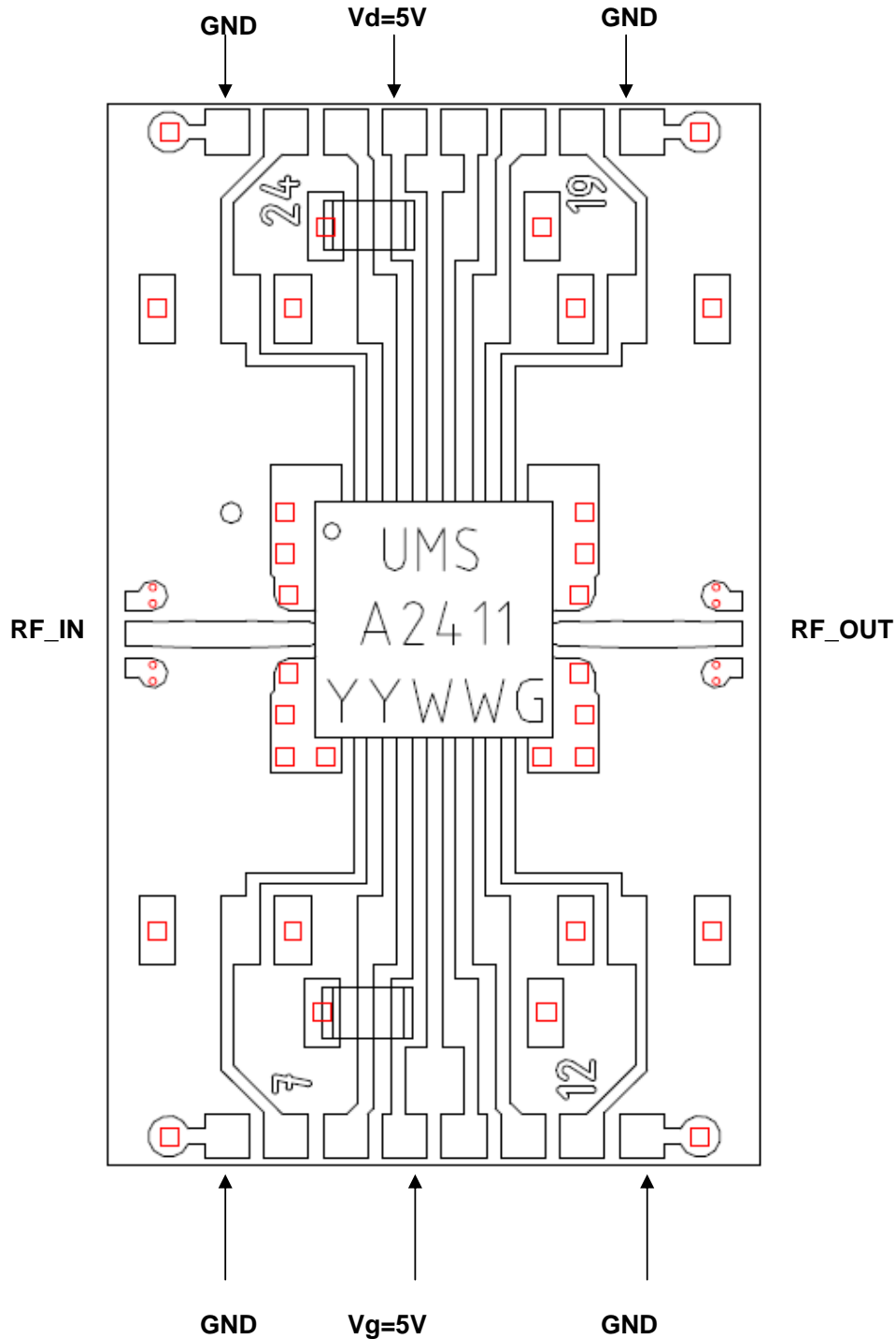
| Rep | P/N | Qt | DESIGNATION | REF FABRICANT | FABRICANT |
|-----|-----------|----|---|------------------|----------------------------------|
| | 614.95564 | 1 | Monture 30X30 EDG | SEMELLE | (Sous traitance mecanique) |
| | 614.95541 | 1 | Demonstrateur Board 24L QFN4X4 | CIRCUIT 95541 | (Sous traitance Circuit Imprimé) |
| | 4.7000774 | 2 | Connecteur SMA (DC-28GHz) | PSF-S03-000-01 | GIGALANE |
| | 614.95570 | 2 | Adaptateur connecteur PSF-S03-000-01 | FOURCHE | |
| | | 4 | Vis CL M2.5X3 | | |
| | | 2 | Condo 0603 X7R 10nF ±10% 50V | GRM1888R71H103K | MURATA |
| | | 2 | Barette male 7x2 Contacts pl. 614.97366 | 4.730334.1804.00 | Kontek COMATEL |
| | | 1 | CHA2411QDG | | |

Ref. : DSCHA2411-QDG8333 - 28 Nov 08

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Specifications subject to change without notice

Recommended Test Fixture (Ref. 95581) for measurements in the package's plans with probes



ESD sensitivity

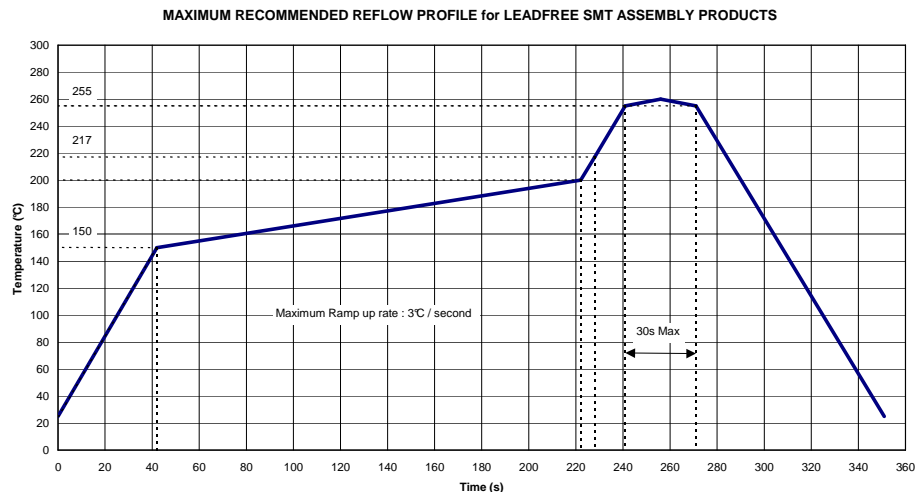
| Standard | Value |
|-----------------|---------------------------|
| MIL-STD-1686C | HBM Class 1 (<0V - 1999V) |
| ESD STM5.1-2001 | HBM Class 0 (<250V) |

Package Information

| Parameter | |
|-----------------------|--|
| Package body material | RoHS-compliant Low stress Injection Molded Plastic |
| Lead finish | 100% matte Sn |
| MSL Rating | MSL1 |

Recommended surface mount package assembly(see UMS AN0017)

For volume production the SMD type package can be treated as a standard surface mount component (please refer to the IPC/JEDEC J-STD-020C standard or equivalent). The assembly on the motherboard can be performed using a standard assembly process (e.g. stencil solder printing, standard pick-and-place machinery, and solder reflow oven). However, caution should be taken to perform a good and reliable contact over the whole pad area.

**Caution**

The solder thickness after reflow should be typical 50µm [2 mils] and the lateral alignment between the package and the motherboard should be within 50µm [2 mils].

It is important for the performance of the product that the whole overlapping area between the motherboard and package pads is connected. Voids or other improper connections, in particular, between the ground pads on motherboard and package will lead to a deterioration of the RF performance and the heat dissipation. The latter effect can reduce drastically reliability and lifetime of the product.

Ordering Information

24L-QFN4x4 Lead Free Package: CHA2411-QDG/XY

Stick: XY=20 Tape and reel: XY=21

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